

RSC Unaxis 790 PECVD

Recipe	Deposition Rate (nm/min)	Temperature	Refractive index (@632nm)	Etch rate in 6:1 BOE (nm/min)	Stress (MPa)
SiO2	64	350C	1.46	220	420 compressive
SiN	11.7	350C	1.98	11.6	119 compressive
PT_SiC	4.5	350C	2.52		